

N-CHANNEL MOS FIELD EFFECT TRANSISTOR  
FOR SWITCHING

DESCRIPTION

The  $\mu$ PA1855 is a switching device which can be driven directly by a 2.5 V power source.

The  $\mu$ PA1855 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- Can be driven by a 2.5 V power source
- Low on-state resistance  
 $R_{DS(on)1} = 23 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 3.0 \text{ A)}$   
 $R_{DS(on)2} = 24 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.0 \text{ V, } I_D = 3.0 \text{ A)}$   
 $R_{DS(on)3} = 29 \text{ m}\Omega \text{ MAX. (} V_{GS} = 2.5 \text{ V, } I_D = 3.0 \text{ A)}$
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
$\mu$ PA1855GR-9JG	Power TSSOP8

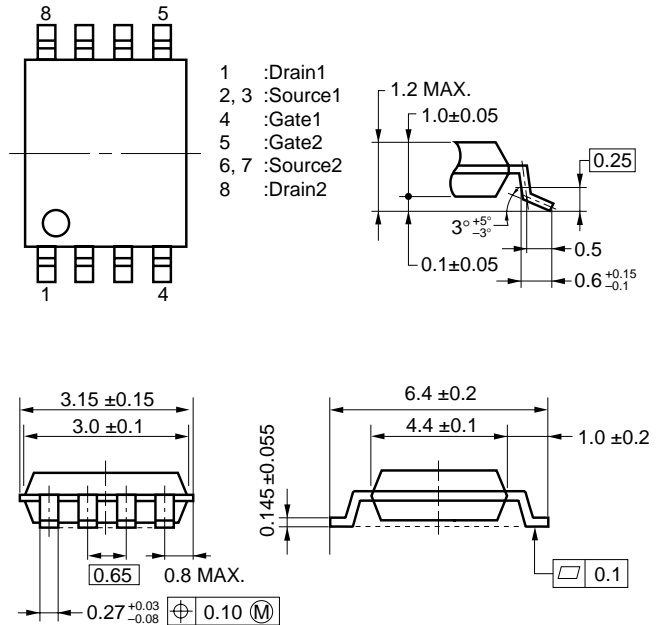
ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Drain to Source Voltage	V <sub>DSS</sub>	20	V
Gate to Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (DC)	I <sub>D(DC)</sub>	±6.0	A
Drain Current (pulse) <sup>Note1</sup>	I <sub>D(pulse)</sub>	±24	A
Total Power Dissipation <sup>Note2</sup>	P <sub>T</sub>	2.0	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

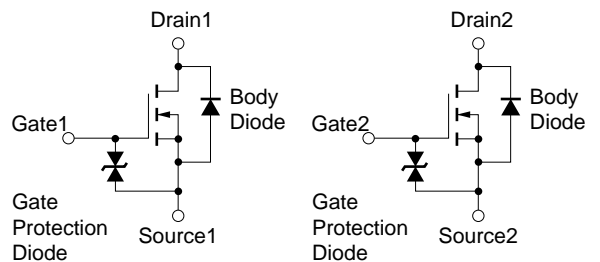
- Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1 %  
 2. Mounted on ceramic substrate of 5000 mm<sup>2</sup> x 1.1 mm

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

PACKAGE DRAWING (Unit : mm)



EQUIVALENT CIRCUIT

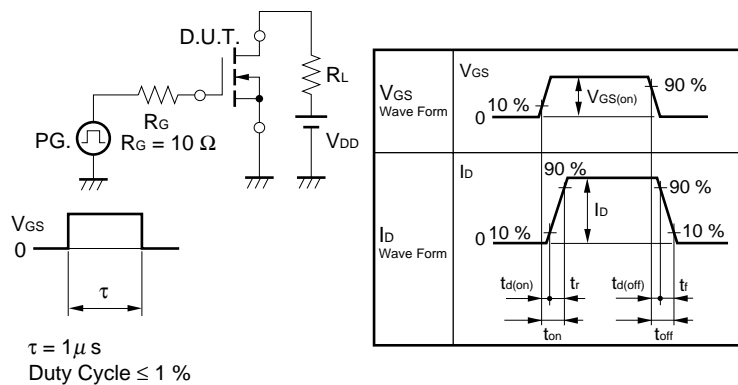


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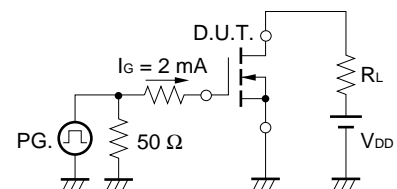
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			10	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	0.5	1.0	1.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.0 A	1	13.3		S
Drain to Source On-state Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.0 A		17	23	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = 4.0 V, I <sub>D</sub> = 3.0 A		18	24	mΩ
	R <sub>DS(on)3</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 3.0 A		22	29	mΩ
Input Capacitance	C <sub>iSS</sub>	V <sub>DS</sub> = 10 V		980		pF
Output Capacitance	C <sub>oSS</sub>	V <sub>GS</sub> = 0 V		293		pF
Reverse Transfer Capacitance	C <sub>rSS</sub>	f = 1 MHz		205		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V		86		ns
Rise Time	t <sub>r</sub>	I <sub>D</sub> = 3.0 A		247		ns
Turn-off Delay Time	t <sub>d(off)</sub>	V <sub>GS(on)</sub> = 4.0 V		480		ns
Fall Time	t <sub>f</sub>	R <sub>G</sub> = 10 Ω		659		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = 10 V		8.8		nC
Gate to Source Charge	Q <sub>GS</sub>	I <sub>D</sub> = 6.0 A		2.2		nC
Gate to Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> = 4.0 V		3.2		nC
Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 6.0 A, V <sub>GS</sub> = 0 V		0.82		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 6.0 A, V <sub>GS</sub> = 0 V		44		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 15 A/μs		2.2		nC

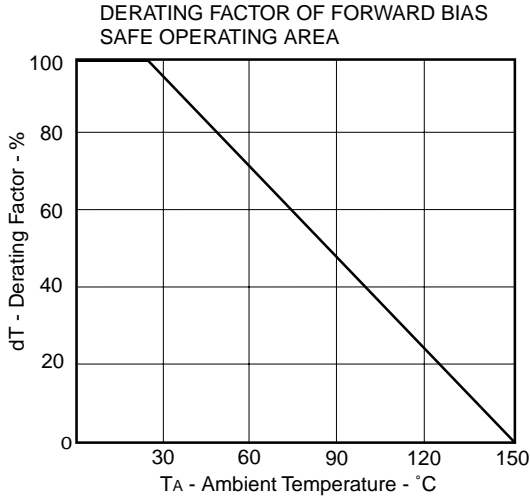
**TEST CIRCUIT 1 SWITCHING TIME**



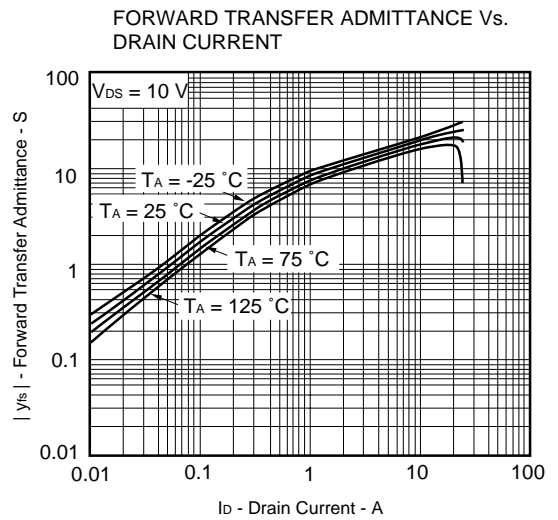
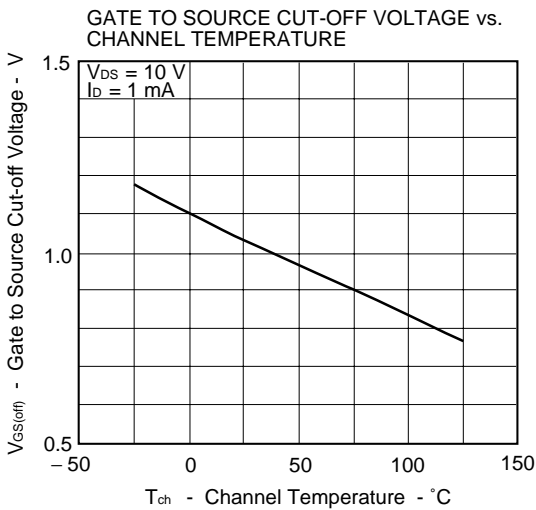
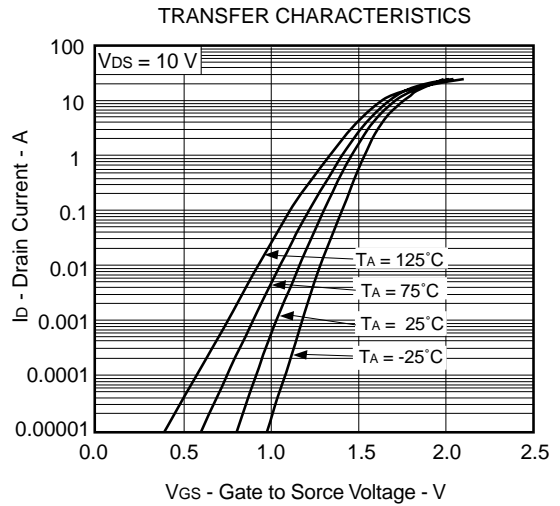
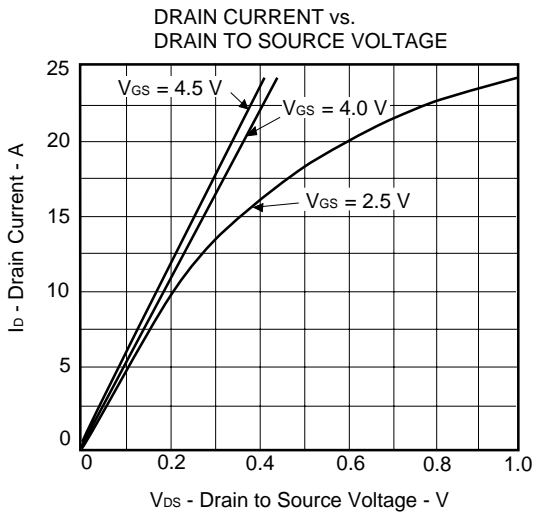
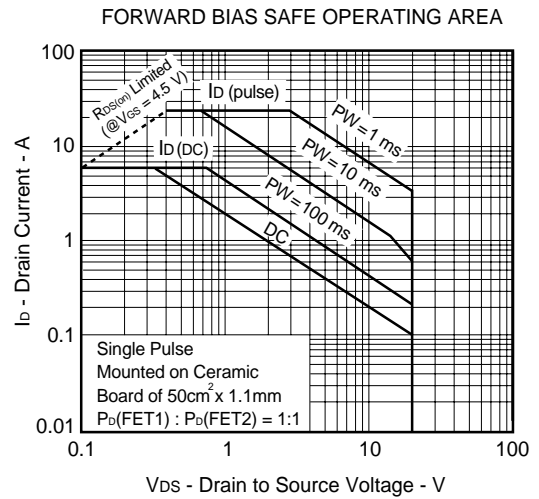
**TEST CIRCUIT 2 GATE CHARGE**

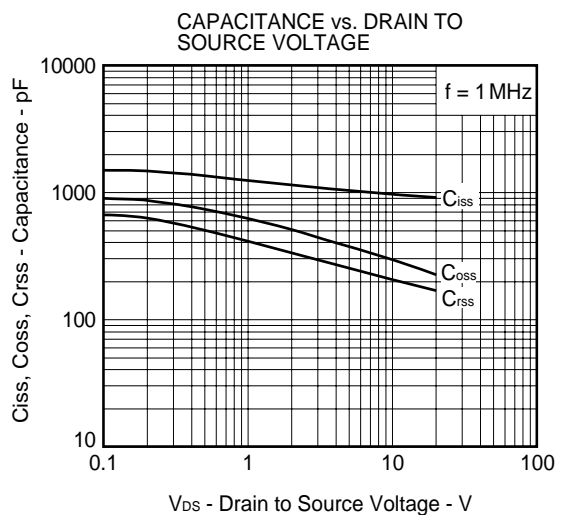
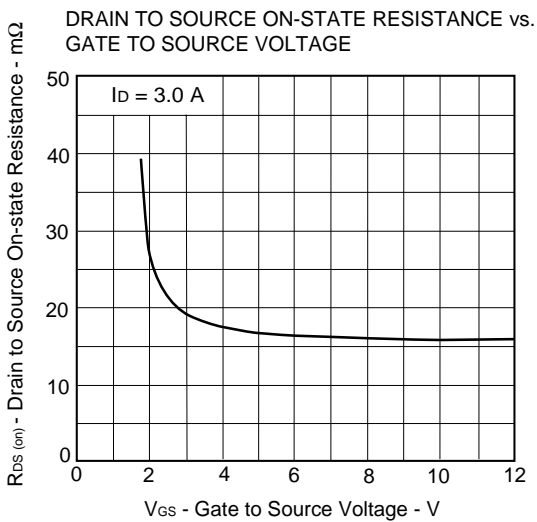
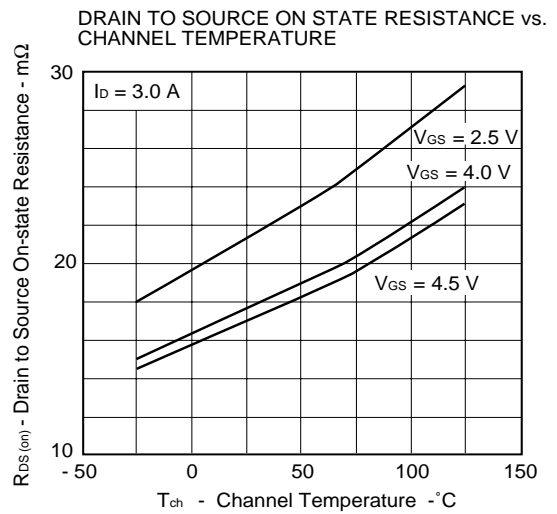
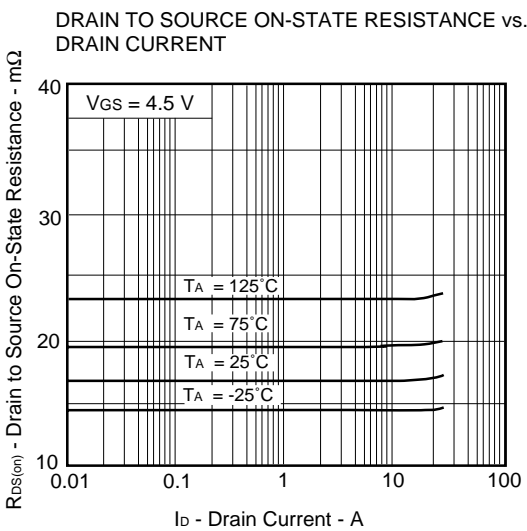
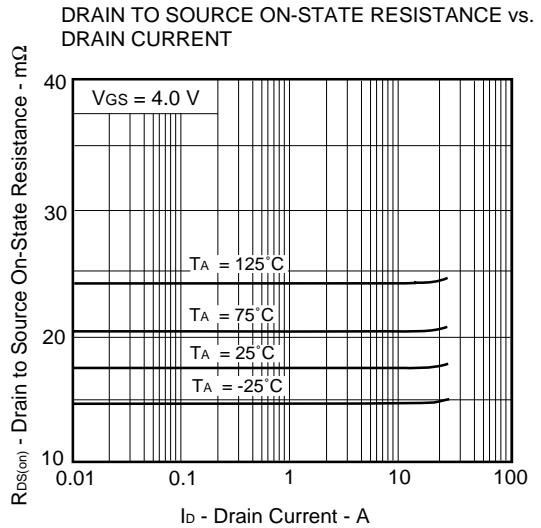
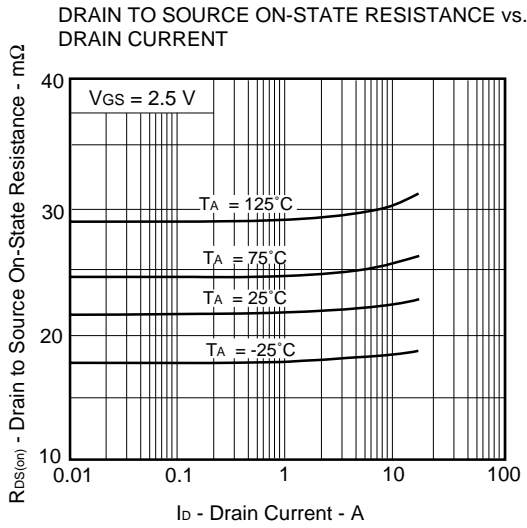


TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )

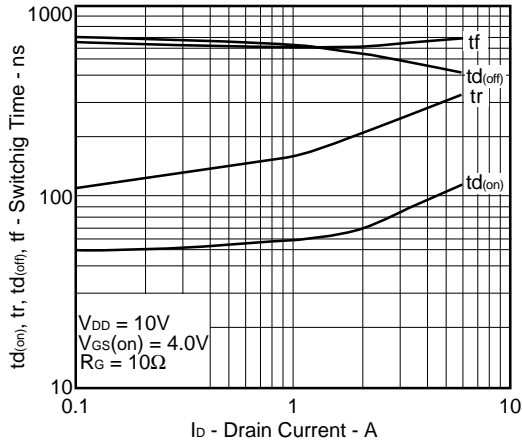


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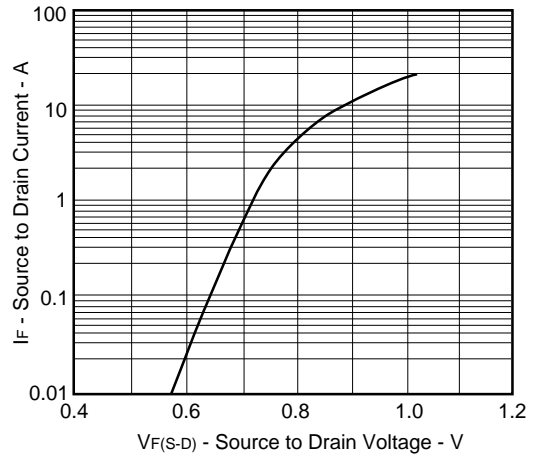




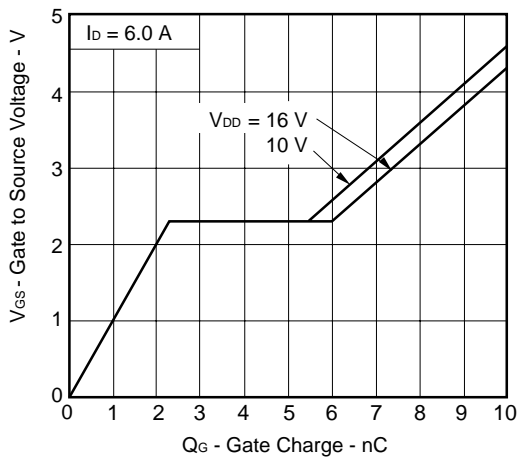
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

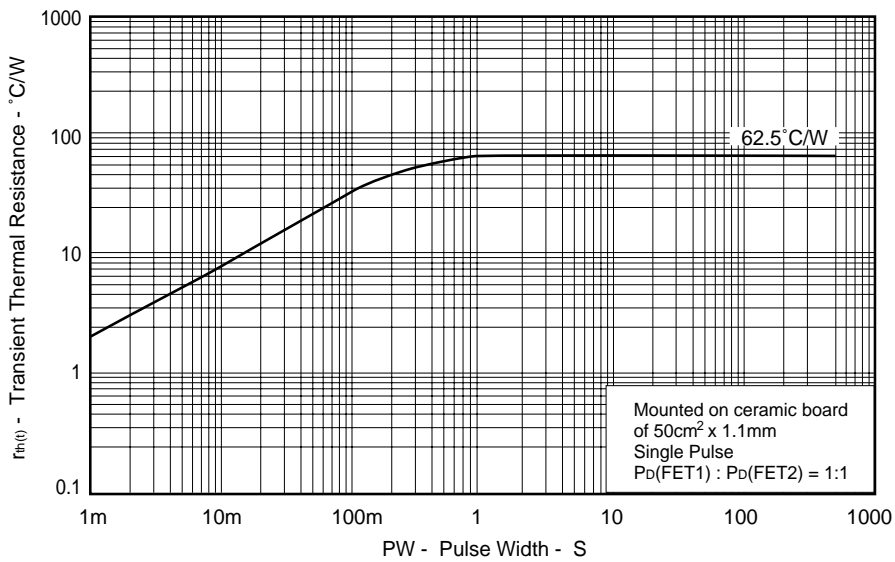


DYNAMIC INPUT CHARACTERISTICS



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TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



[MEMO]

[MEMO]

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